

Application No. 10/724,201
Amendment dated November 23, 2005
Reply to Office Action of August 23, 2005

Docket No.: 0941-0872P

REMARKS

Claims 1-21 remain present in this application.

The specification and claims 15, 20 and 21 have been amended, and claims 1-14 are currently withdrawn from consideration. Reconsideration of the application, as amended, is respectfully requested.

Objection to the Claims

Claims 20 and 21 stand objected to for certain informalities. In view of the foregoing amendments, it is respectfully submitted that these informalities have been addressed. Reconsideration and withdrawal of any objection to the claims are respectfully requested.

Rejections under 35 USC 102(e) and 103

Claims 15-20 stand rejected under 35 USC 102(e) as being anticipated by Hsu et al., US Publication 2004/0067640. This rejection is respectfully traversed.

Claim 21 stands rejected under 35 USC 103 as being unpatentable over Hsu et al., in view of Gotkis et al., U.S. Publication 2004/0058620. This rejection is respectfully traversed.

The Examiner asserts that Hsu discloses the claimed CMP rework method.

It is noted, however, that independent claim 15 of the present application recites (emphasis added):

“A CMP rework method, comprising the steps of:
providing a semiconductor substrate which has a patterned dielectric layer,
a barrier layer over the patterned dielectric layer, and a conductive layer over the
barrier layer;
performing a first CMP process to remove part of the conductive layer;

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depositing a layer of material *with a planar surface* substantially the same as the conductive layer over the conductive layer; and
performing a second CMP process to expose the patterned dielectric layer."

It is clear that the CMP rework method in independent claim 1 comprises depositing a layer of material *with a planar surface* substantially the same as the conductive layer over the conductive layer.

However, Hsu discloses that the second cooper layer 28B is blanket deposited conformally over the first cooper layer 28A. As FIG. 1E shows, the surface of the second cooper layer 28B is **not planar**. Accordingly, it should be obvious to one of ordinary skill in the art that the CMP rework method of the present application is different from the CMP rework method of Hsu.

It is therefore respectfully submitted that the CMP rework method of the present application is neither taught nor suggested by the prior art utilized by the Examiner. Accordingly, reconsideration and withdrawal of the 35 USC 102(e) and 103 rejections are respectfully requested.

Conclusion

Favorable reconsideration and an early Notice of Allowance are earnestly solicited.

In the event that any outstanding matters remain in this application, the Examiner is invited to contact the undersigned at (703) 205-8000 in the Washington, D.C. area.

Birch, Stewart, Kolasch & Birch, LLP

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If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Dated: November 23, 2005

Respectfully submitted,

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